REMARKS

Claims 2-17 are pending in the application with claims 2, 4, 6, 8, 10, 12, 14 and 16 being independent. Claims 2, 4, 6, 8, 10 and 12 have been amended. Support for the amendments may be found throughout the application, including Fig. 1B and its accompanying description. No new matter has been added.

Applicant notes, with appreciation, the allowance of claims 14-17. Claims 14-17 have not been amended and remain pending.

Claims 2-13 have been rejected under 35 U.S.C. § 102(b) as being anticipated by U.S. Patent No. 5,508,533 ("Takemura").

Referring to independent claim 2, applicant respectfully requests reconsideration and withdrawal of the rejection as Takemura does not describe or suggest "providing said first and second regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film through the two openings of the mask...wherein crystals grow from said first region to said second region and the growth of the crystals terminates at said second region," as recited in claim 2.

In Takemura, heavily doped regions 105 are formed from slits in a mask 104. *See* Takemura, Fig. 1B. The heavily doped regions 105 are used to grow crystals towards each other. *See* Takemura, column 4, lines 18-33. Notably, the crystals grow to a crystal grain boundary 105' between the two heavily doped regions. *See* Takemura, Fig. 1B and column 4, lines 28-30.

As recited by independent claim 2, the mask has two openings to expose a first region and a second region of the semiconductor film. Moreover, crystals grow from the first region to the second region and the growth of the crystals terminates at the second region. Takemura, however, does not grow crystals from it first heavily doped region 105 formed (from a slit in the mask) terminating at its second heavily doped region 105 (also formed from a slit in the mask). Rather, Takemura's crystal growth is to the intermediary crystal grain boundary 105'. Specifically, Takemura states "[c]rystals grown from two regions met each other, thus forming a crystal grain boundary 105.'" *See* Takemura, Fig. 1B (showing the crystal grain boundary 105' as between the heavily doped regions 105) and column 4, lines 28-30.

Consequently, Takemura does not describe or suggest "providing said first and second regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film through the two openings of the mask...wherein crystals grow from said first region to said second region and the growth of the crystals terminates at said second region," as recited by amended claim 2. For at least these reasons, the rejections of independent claim 2 and its dependent claim 3 should be withdrawn.

Independent claim 4 also recites "providing said first and second regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film through the two openings of the mask...wherein crystals grow from said first region to said second region and the growth of the crystals terminates at said second region." Accordingly, the rejection of independent claim 4 and its dependent claim 5 should be withdrawn for the reasons discussed above with respect to claim 2.

Amended independent claims 6 and 8 recite "providing said first and second regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film through the two openings of the mask...wherein said second region functions as a stopper for terminating the crystallization from said first region." As discussed above with respect to claim 2, Takemura grows crystals to an intermediary crystal grain boundary 105'. Consequently, Takemura does not describe or suggest said second region functions as a stopper for terminating the crystallization from said first region, and for similar reasons as above, the rejection of independent claims 6 and 8 and their dependent claims 7 and 9 should be withdrawn.

Amended independent claims 10 and 12 recite "providing said first and second stripe-shaped regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film through the two openings of the mask...wherein said second stripe-shaped region functions as a stopper for terminating the crystallization from said first stripe-shaped region." As such, the rejection of independent claims 10 and 12 and their dependent claims 11 and 13 should be withdrawn for the reasons discussed above with respect to claims 6 and 8.

No other matters being raised, it is believed that all claims are in condition for allowance and such action is courteously solicited.

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Respectfully submitted,

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